

# Thermal stabilization of an active alumina and effect of dopants on the surface area

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The  $\alpha$ - $\text{Al}_2\text{O}_3$  transformation of a monolithic active alumina has been increased from 1200 to  $\sim 1380^\circ\text{C}$  through structural incorporation of silica. This shift is significant since  $\alpha$ - $\text{Al}_2\text{O}_3$  transformation determines the limits of the usefulness of these materials as catalysts and catalyst carriers. The thermal stabilization effect is optimized at around 6% silica doping. At elevated temperatures, the material containing no silica rapidly loses surface area, primarily by  $\alpha$ - $\text{Al}_2\text{O}_3$  transformation, whereas the material containing excess silica loses surface area by classical sintering.

## 1. Introduction

Transition aluminas have high surface areas and are well known for their catalytic properties [1-4]. The maximum temperature limits for the various forms of these high surface area aluminas have been reported as follows: gamma,  $850^\circ\text{C}$ ; delta,  $1150^\circ\text{C}$ ; theta,  $1150^\circ\text{C}$ , alpha being the only stable phase above  $1150^\circ\text{C}$  [5]. The transformation to the alpha phase marks the end of the useful catalytic properties of these materials since activated sintering (the Hedvall effect) causes a catastrophic decrease in surface area. Some of the recent application, particularly the high temperature catalytic carrier application for auto emission control, require service temperatures close to the thermal stability limit of these materials; therefore, there is an industrial need to stabilize the high surface area aluminas. Various investigators have studied the effect of dopants on the alumina transformations [6-15].

The monolithic active alumina which is employed in this investigation has been previously reported [16]. This material upon transforming to  $\alpha$ - $\text{Al}_2\text{O}_3$  at  $1200^\circ\text{C}$  becomes opaque, without losing its monolithic nature. This makes it possible to follow the effect of dopants on the  $\alpha$ - $\text{Al}_2\text{O}_3$  transformation visually, as well as with DTA and X-ray analysis. It is found that introduction of some dopants into the material, e.g.  $\text{ThO}_2$ ,  $\text{ZrO}_2$ ,

and  $\text{SiO}_2$  increases the  $\alpha$ - $\text{Al}_2\text{O}_3$  transformation temperature while the introduction of certain others, e.g.  $\text{TiO}_2$  and  $\text{Na}_2\text{O}$  decrease it. Since the primary goal of this investigation was the formation of a refractory high surface area material, only those dopants which contributed to the crystalline stability as well as minimized the sintering of the material were investigated. Among these, silica was found to be especially effective and was studied in greater detail.

## 2. Experimental procedure

### 2.1. Sample preparation

The high surface area monolithic alumina studied is produced from a clear sol of aluminium monohydroxide. The precursor sol was prepared by hydrolysis of aluminium-secondary butoxide,  $\text{Al}(\text{OC}_4\text{H}_9^s)_3$ , and peptization of the resultant monohydroxide with 0.07 mol nitric acid per mol alkoxide [17, 18]. The methods of introducing a second oxide into this system, the limits of such additions, and the rules governing the capability of these gels to remain monolithic during the drying and pyrolysis have been presented earlier [19, 20]. The method used provides intimate mixing of the constituents; and in certain cases, e.g. with silica, a chemical bond formation and polymerization among the constituents also occurs. The method of preparation is particularly import-

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ant in this system. In classical methods of sample preparation from oxide powder mixes, crystalline transformation may take place in either alumina or silica phase before a substantial reaction between these two refractory oxides occur.

The doped sols were gelled, dried, and pyrolyzed. The samples were heated together in the same furnace, and small portions were taken out at various temperatures and time intervals for investigation.

## 2.2. Test methods

The surface areas of samples were determined by the standard BET method, which makes use of nitrogen adsorption desorption isotherms. The temperature of the  $\alpha$ - $\text{Al}_2\text{O}_3$  transformation of the active alumina studied can be identified by a sharp exothermic DTA peak [16]. The effect of doping on the transformation has, therefore, been investigated by differential thermal analysis as well as X-ray diffraction. The DTA equipment had a platinum/rhodium liquid-type sample holder with embedded Pt/Rh thermocouples. Samples of approximately 100 mg were heated  $10^\circ\text{C min}^{-1}$  in an air atmosphere. It was also possible to observe the crystalline transformation visually since as mentioned, it is accompanied by the loss of transparency in these monolithic samples.

## 3. Results and discussion

The effect of 4% doping of the material with various oxides on the exothermic DTA peak associated with the transformation of the undoped material at  $1200^\circ\text{C}$  was first surveyed. Oxides of the following elements were studied: K, Na, Li, Ba, Sr, Ca, B, La, Ti, Th, Zr and Si. Ba and Sr broaden this exothermic peak; Na, Ti, K and B progressively showed lower temperature DTA peaks; Ca and Li had endothermic DTA peaks around  $700$  and  $1150^\circ\text{C}$  respectively. All the above samples had a low surface area after the occurrence of the DTA peak. Only Th, Zr and Si had a thermal stabilization effect beyond  $1200^\circ\text{C}$ , thus no further work was done on the other dopants.

The surface area measurements of samples doped with 4%  $\text{ThO}_2$ ,  $\text{ZrO}_2$ , and  $\text{SiO}_2$  after a 24 h heat-treatment at  $1000^\circ\text{C}$  were 99, 98 and  $151\text{ m}^2\text{g}^{-1}$  respectively. Undoped samples give a surface area of approximately  $80\text{ m}^2\text{g}^{-1}$  for the same heat-treatment.

The thermal stabilizing effect of thoria, hafnia and silica on active aluminas has been reported

elsewhere [10-14]; and a similar effect from zirconia is also expected. However, the magnitude of the stabilization effect of silica on this material was somewhat unexpected; therefore, further work was concentrated entirely on silica doping.

### 3.1. Effect of silica on the $\alpha$ -alumina transformation temperature

Since the primary cause of surface area loss in undoped alumina is the transformation to  $\alpha$ - $\text{Al}_2\text{O}_3$  the effect of silica doping on this transformation was investigated. DTA runs show that an increase in the silica concentration initially causes a corresponding increase in  $\alpha$ - $\text{Al}_2\text{O}_3$  transformation temperature (Fig. 1). When the DTA peak temperatures are plotted as a function of silica concentration, a curve showing the maximum stabilization temperature of about  $1380^\circ\text{C}$  is obtained around 6%  $\text{SiO}_2$  (Fig. 2). With additions beyond 6%, a decrease in the temperature of the DTA peak as well as in its relative intensity is observed.

The sharp DTA peak of the undoped material occurring at  $1200^\circ\text{C}$  was previously determined to be the result of  $\alpha$ - $\text{Al}_2\text{O}_3$  transformation [16]. There may be questions whether, with the silica doping, these DTA peaks still represent the  $\alpha$ - $\text{Al}_2\text{O}_3$  transformation. The DTA peaks must still represent the  $\alpha$ - $\text{Al}_2\text{O}_3$  transformation at low silica concentrations, e.g. below 6%, for several reasons. 2% silica-doped material gives a DTA peak at around  $1360^\circ\text{C}$  and no peak is observed at  $1200^\circ\text{C}$  (Fig. 1). If we assume, for example, that this new

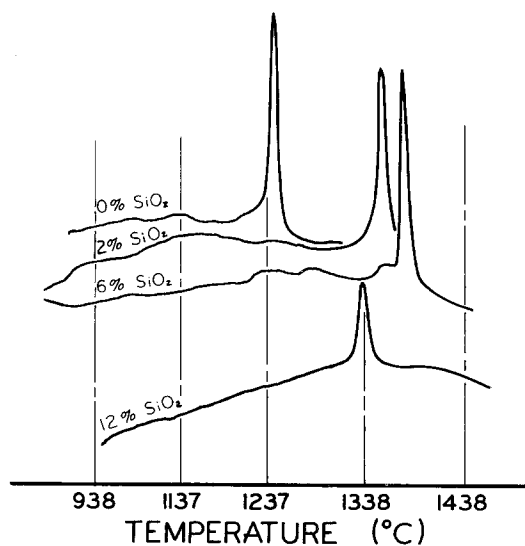


Figure 1 The DTA curves of the material doped with various amounts of silica ( $10^\circ\text{C min}^{-1}$  heating rate, in air).

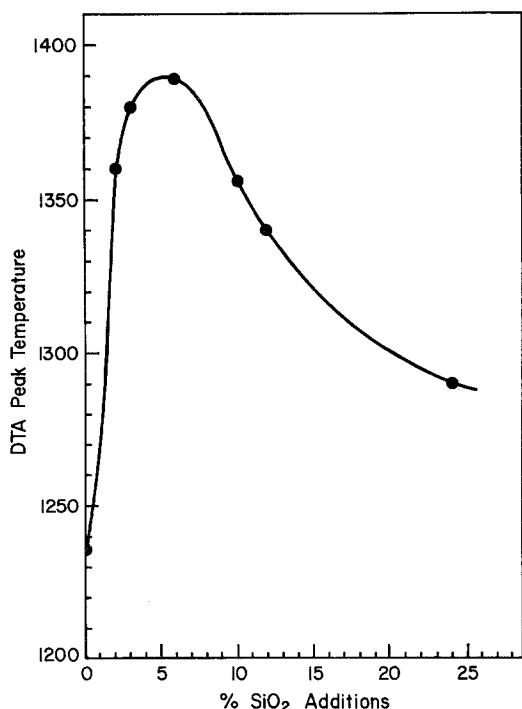


Figure 2 The effect of SiO<sub>2</sub> concentration on the DTA peak temperature. (For accuracy's sake the tip of the DTA peak rather than the starting point is used.)

DTA peak is due to mullite formation, then there has to be another peak at 1200°C, since over 90% of the active Al<sub>2</sub>O<sub>3</sub> must still remain free and transform to α-Al<sub>2</sub>O<sub>3</sub> (with 2% SiO<sub>2</sub> the maximum theoretical mullite formation can only be 7%). Under this condition any assumptions that perhaps the mullite stabilizes the material cannot be justified either, since the mullite formation temperature would be higher than the α-Al<sub>2</sub>O<sub>3</sub> transformation temperature.

It is quite possible, that the DTA peaks occurring above 6% SiO<sub>2</sub> concentration are of entirely different origin and are due to mullite formation. Nevertheless, the fact that the DTA peaks represent the α-Al<sub>2</sub>O<sub>3</sub> transformation below the 6% SiO<sub>2</sub> concentrations is established experimentally by making X-ray analysis of the material before and after the occurrence of the DTA peak (see X-ray diffraction section and Fig. 5).

### 3.2. Effect of silica on the thermal stability of the surface area

Table I gives the surface areas of samples doped with various amounts of silica as a function of concentration and time at 1100°C, along with the calculated percent of surface area retained between intervals of 30 to 400 h.

TABLE I Effect of incorporation of silica on the stability of the surface area after firing for various times at 1100°C

%SiO <sub>2</sub>	Surface area (m <sup>2</sup> g <sup>-1</sup> )			%Surface area retained (30 to 400 h)
	30h	100h	400h	
1	44.7	21.9	13.6	30
3	92.3	71.9	52.8	57
5	108.0	91.7	77.9	72
7	116.0	98.4	84.9	73
10	133.0	107.0	88.7	67

The reason the samples containing higher silica initially show higher surface area is largely due to the source of the silica and method of sample preparation. The silica obtained from hydrolyzed ethyl silicate has a high surface area; however, it sinters rather rapidly if not tied into the structure. The ability to retain surface area is greatest at 5 to 7% SiO<sub>2</sub>. The optimizing effect of about 6% silica concentration on the thermal stability of the surface area becomes evident after sufficiently long periods of time at 1100°C, e.g. 400 h (Fig. 3). The 2000 h curve of Fig. 3, which was obtained by extrapolating the surface areas shown in Table I, to 2000 h at constant silica concentrations, makes this even more evident. Therefore, the surface stabilization effect of SiO<sub>2</sub> parallels its effect on the α-Al<sub>2</sub>O<sub>3</sub> transformation.

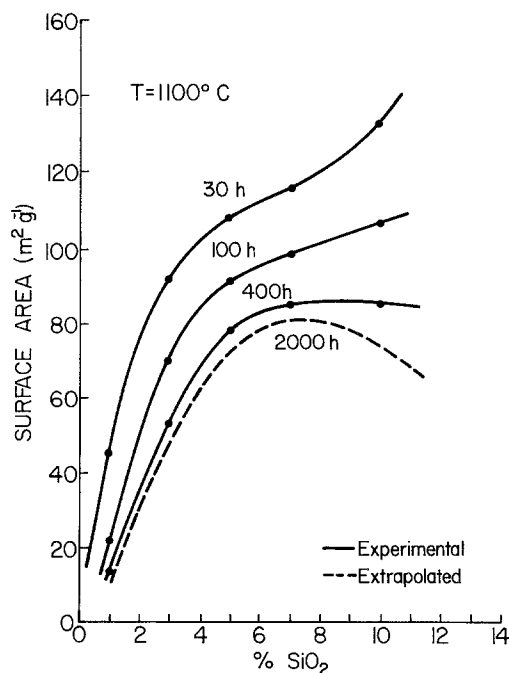


Figure 3 The surface area of the material as a function of SiO<sub>2</sub> content and time at 1100°C. (The 2000 h curve was obtained by extrapolating the data of Table I at constant silica concentrations in log time scale.)

### 3.3. X-ray diffraction studies

A detailed structural study of the undoped alumina including infra-red and electron spectroscopy, X-ray diffraction, and small-angle X-ray scattering has been presented earlier [16].

The X-ray diffraction pattern of undoped material gives agreement for  $\delta$ - $\text{Al}_2\text{O}_3$  with respect to the number and position of reflections observed. However, relative intensities of these reflections are appreciably different from the reported values of  $\delta$ - $\text{Al}_2\text{O}_3$  (ASTM pattern number 16-394). In monolithic samples this is generally an indication of preferred orientation of crystallites. However, our pulverized samples gave the similar results. This deviation may be an indication of a defect structure, e.g. having vacancies or displaced atoms in each unit cell [16]. Such variations are commonly observed in transition aluminas [21-24].

X-ray diffraction patterns of samples doped with various amounts of silica and heat-treated at  $800^\circ\text{C}$  for 1 h show that the relative areas under the two primary peaks occurring at  $45.5$  and  $65.5^\circ$  do not change up to 5 to 6% silica concentration. Whereas, additions above this concentration cause a rapid decrease of the area under these peaks.

Fig. 4 shows X-ray patterns of samples heated 30 h at  $1100^\circ\text{C}$ . Only the 1%  $\text{SiO}_2$ -doped sample showed the presence of the  $\alpha$ -alumina phase. Undoped material would have principally transformed to  $\alpha$ - $\text{Al}_2\text{O}_3$ . When the heat-treatment period was extended to 400 h still there was no indication of  $\alpha$ - $\text{Al}_2\text{O}_3$  formation in the remaining samples (Table II).

3 and 6% silica-doped samples were heated at  $1350$  and  $1400^\circ\text{C}$  for 10 min—temperatures just

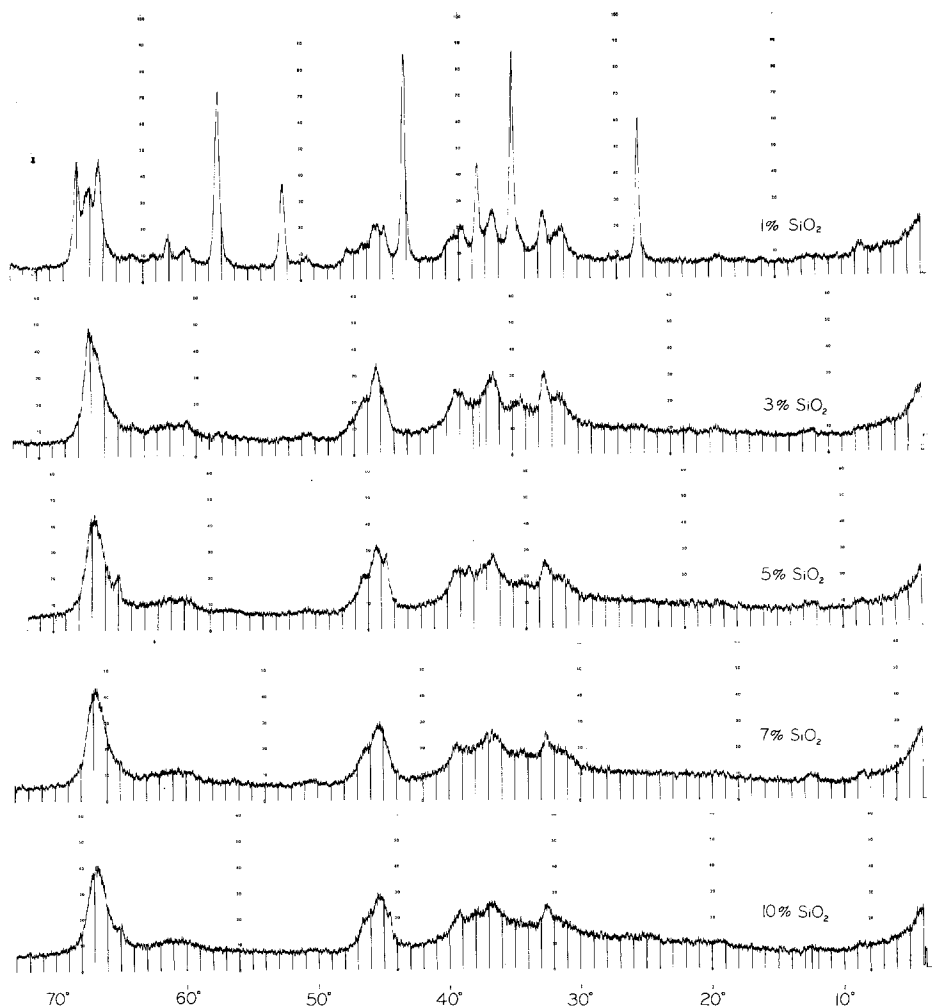


Figure 4 The X-ray diffraction patterns of various amounts of  $\text{SiO}_2$ -doped samples held at  $1100^\circ\text{C}$  for 30 h. (Only 1%  $\text{SiO}_2$ -doped samples show formation of  $\alpha$ - $\text{Al}_2\text{O}_3$ .)

TABLE II X-ray diffraction analysis of SiO<sub>2</sub>-doped material

%SiO <sub>2</sub>	Phases formed at 1100° C	
	30 h	400 h
1	α-Al <sub>2</sub> O <sub>3</sub> P.P.	α-Al <sub>3</sub> O <sub>3</sub> P.P.
	α-Al <sub>2</sub> O <sub>3</sub> T.P.	δ-Al <sub>2</sub> O <sub>3</sub> T.P.
3	α-Al <sub>2</sub> O <sub>3</sub>	δ-Al <sub>2</sub> O <sub>3</sub> P.P.
		A trace of cubic phase with lattice parameters 8.0 (spinel?)
5	δ-Al <sub>2</sub> O <sub>3</sub>	δ-Al <sub>2</sub> O <sub>3</sub>
7	δ-Al <sub>2</sub> O <sub>3</sub>	δ-Al <sub>2</sub> O <sub>3</sub>
10	δ-Al <sub>2</sub> O <sub>3</sub>	δ-Al <sub>2</sub> O <sub>3</sub>

before and after the DTA peaks. X-ray analysis of these samples indicates that the material has the active alumina phase with a trace amount of mullite at 1350° C; whereas, at 1400° C this active phase is entirely transformed to α-Al<sub>2</sub>O<sub>3</sub>. (See Fig. 5 for 6% SiO<sub>2</sub> doping).

The fact that a more stable phase of the transition alumina is formed by 6% silica-doping supports the view that, initially, silica goes into certain sites in the structure causing no disturbance in the lattice and remains essentially undetectable. When

the sites are saturated the structure is more stable, requiring higher energy to transform. Additions of silica above 6% appear to be in excess, presumably having the effect of activating the sintering.

#### 4. Conclusions

(1) Introduction of up to 6% silica into the structure of the monolithic active alumina significantly increases the structural stability. The α-Al<sub>2</sub>O<sub>3</sub> transformation temperature of the material is increased from about 1200° C to about 1380° C at 6% silica doping.

(2) Material containing no silica primarily loses surface area by sintering activated by transformation to α-Al<sub>2</sub>O<sub>3</sub>, whereas material containing excess silica appears to lose surface area by sintering promoted by the presence of silica. The capacity to retain the surface area at elevated temperatures in sustained use is optimized at about 6% SiO<sub>2</sub> doping.

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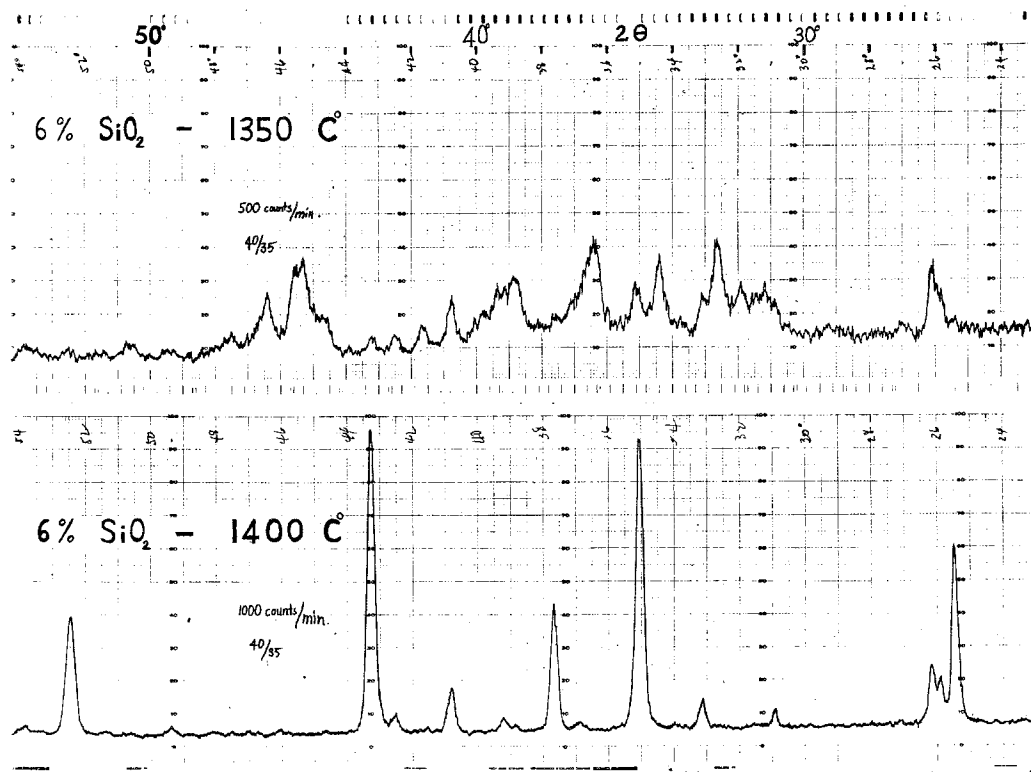


Figure 5 The X-ray diffraction patterns of 6% SiO<sub>2</sub>-doped sample heat-treated at 1350 and 1400° C for 10 min (before and after the transformation DTA peak).

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